Interconnect RC extraction

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What's Capacitance?

 $+\mathbf{Q} - \mathbf{Q}$ $\bigcirc \quad \ddagger \qquad \ddagger \qquad \begin{vmatrix} \vdots \\ \vdots \\ \vdots \end{vmatrix}$

Simplest model: parallel-plate capacitor

- It has two parallel plates and homogeneous dielectric between them
- The capacitance is
 - $-\epsilon$ permittivity of dielectric
 - A area of plate $C = \mathcal{E} \frac{A}{d}$
 - *d* distance between plates
- The capacitance is the capacity to store charge
 - charge at each plate is
 - one is positive, the other is negative

$$Q = CV$$

General Picture



- For multiple conductors of any shapes and materials, and in any dielectric, there is a capacitance between any two conductors
- Each conductor has a resistance associated with it and is calculated using foundry-provided sheet-resistance tables.
- Resistance of a net is calculated independent of its neighbors.

Capacitance Matrix

Capacitance is often written as a symmetric matrix



 $C = \begin{array}{cccc} c_{11} & c_{12} & c_{13} \\ c_{21} & c_{22} & c_{23} \\ c_{31} & c_{32} & c_{33} \end{array}$

 $c_{ii} = -\sum_{j=1}^{m} c_{ij} (j \neq i)$ is the self-capacitance for a conductor • *e.g.*, $c_{11} = c_{12} + c_{13}$

The charge is given by $Q^m = C^{mm} (V^m)^T$

• e.g.,
$$q_1 = c_{11}v_1 - c_{12}v_2 - c_{13}v_3$$

= $c_{12}(v_1 - v_2) + c_{13}(v_1 - v_3)$

Application in VLSI Circuits

- **Conductors: metal wire, via, polysilicon, substrate**
- Dielectrics: SiO₂,...
- Total cap for a wire
 - delay, power
- Mutual cap between wires
 - signal integrity



Characteristics of Capacitance

Coupling capacitance virtually exists only between adjacent wires or crossing wires but more pronounced between layers i and i-2/i+2.



Capacitance can be pre-computed for a set of (localized) interconnect structures using a GOLDEN 3-D field solver extraction tool.



 $C_{i,i-2}$ coupling between victim and aggressor on layer *i*-2



 $C_{i,i}$ lumped capacitance for victim on layer *i*

 $C_{i,i-2}$ coupling between victim and aggressor on layer *i*-2

Shielding Effect of Ground and Neighbors

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laye	r i	$C_{i,i}$	C <i>i</i> , <i>i</i> -2
	no GND	458.4	130.1(28.4%)
	+ GND	486.6	79.49(16.3%)
	+ neighbors	1428	24.77(1.8%)
laye	r <i>i-2</i>		

 $C_{i,i}$ lumped capacitance for victim on layer *i*

C_{*i*,*i*-2} coupling between victim and aggressor on layer *i*-2



Coupling between Layers *i* and *i*-2



2x 4x 8x12x486.6 534.5 581.3 622.2 635.9 C_{*i*,*i*-2} 79.49 48.45 21.99 3.47 2.47

lumped capacitance for victim on layer *i* coupling between victim and aggressor on layer i-2



Effect of Non-immediate Neighbors (Second Aggressor)



$C_{i,i}$	1436
C_1	616.6
Cr	616.5

 $C_{i,i}$: lumped capacitance for victim.

Effect of Non-immediate Neighbors (Second Aggressor)



$C_{i,i}$	1436	1436(0%)
C_1	616.6	639.8(+3%)
Cr	616.5	639.5(+3%)

 $C_{i,i}$: lumped capacitance for victim.

Table Generation for Lateral, Area andFringe Capacitances



Functions of (w,s)
Pre-computed for per-side per unit-length



Table Generation forCrossing Capacitances



Function of (w,s,wc,sc)







Per-side fringe capacitance = $C_F(w,s_1) * L_1$



2 Add in Per-Side Area, Fringe and Lateral Capacitances



BFind All Crossovers and Crossunders







One-corner crossover correction = $C_{over}(w,s_1,w_c,s_c)$







One-corner crossover correction = $C_{over}(w,\infty,w_c,s_c)$

Summary of Capacitance Extraction

- Find nearest neighbors on the same layer
- Add in per-side lateral, area and fringe capacitances w.r.t. each neighbor
- Sind all crossovers and crossunders
- Add in crossing capacitances corner-by-corner w.r.t. each crossover and crossunder

Sum of capacitance components in above steps is the lumped capacitance of the victim.

References

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